# **EECS151: Introduction to Digital Design and ICs**

## Lecture 16 - Wires, Energy

## **Bora Nikolić**

## Apple Announces M1 Pro & M1 Max: Giant New SoCs with All-

Out Performance
Out Performance
Corbber 18, 2021, AnondTech - The M1 Pro and Max both follow-up on
last year's M1, Apple's first generation Mac silicon that whered in the
beginning of Apple's journey to replace x86 based chips with their own
in-house designs. The M1 had been widely successful for Apple,
showcosing fantastic performance at never-before-seen power efficiency
in the lappap market. Although the M1 was fast, it was still a somewhat







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#### Review

- Two delay components in logical effort:
  - Parasitic delay (p)
  - Effort delay (F)
    - Logical effort (g): intrinsic complexity of the gate
    - Electrical effort (h): load capacitance dependent
- To minimize the delay all stages should have the same effort (h)
- Ideal effort is 4





#### Wires

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#### A modern technology is mostly wires

- Transistors are little things under the wires
- Many layers of wires
- Wires are as important as transistors
  - Speed and power





### Wire Resistance

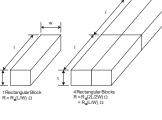
•  $\rho = resistivity (\Omega^*m)$ 

$$R = \frac{\rho}{t} \frac{l}{w} = R_{\Box} \frac{l}{w}$$

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- $R_{\square} = sheet\ resistance\ (\Omega/\square)$ 
  - □ is a dimensionless unit(!)
- Count number of squares
  - R = R<sub>□</sub> \* (# of squares)

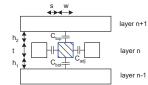




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#### Wire Capacitance

- Wire has capacitance per unit length
  - To neighbors
  - To layers above and below



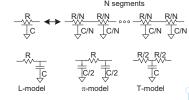


Wire Delay

### Wire RC Model

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- Wires are a distributed system
  - Approximate with lumped element
- 3-segment pi-model is accurate to 3% in simulation





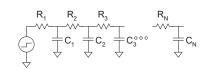








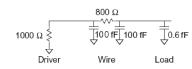
### Elmore Delay for RC Tree



$$\begin{split} t_{pd} &\approx \sum_{\text{nodes } i} R_{i-to-source} C_i \\ &= R_1 C_1 + \left(R_1 + R_2\right) C_2 + \ldots + \left(R_1 + R_2 + \ldots + R_N\right) C_N \end{split}$$

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#### Example: RC Delay with Wire and Gate

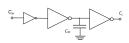




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#### Logical Effort with Wires



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#### Administrivia

- Homework 6 due this week
  - Homework 7 next week
- All labs need to be checked off by next week!
- Projects (ASIC and FPGA) start this week
- Midterm 2 is on November 4 at 7pm
- Courses:
  - EECS251B will be offered in Spring (pending Campus approval)
  - EE194/290C SoC Design

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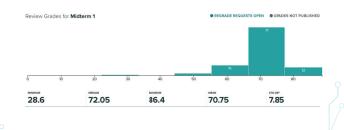
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#### Midterm 1 Scores

EECS151: Average: 69.7/84 (83%) EECS251B: Average 86.4/88 (83%)



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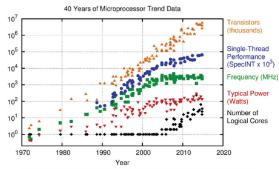


Energy

**Processor Frequency Scaling** 

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riginal data up to the year 2010 collected and plotted by M. Horowitz, F. Labonte, O. Shacham, K. Olukotun, L. Hammond, and C. Batten

Power and Energy

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- $^{\bullet}$  Power is drawn from a voltage source attached to the  $\mathrm{V}_{\mathrm{DD}}$  pin(s) of a chip.
- Instantaneous Power: P(t) = I(t)V(t)
- Energy:  $E = \int_{0}^{T} P(t)dt$
- Average Power:  $P_{\text{avg}} = \frac{E}{T} = \frac{1}{T} \int_{0}^{T} P(t) dt$

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#### Power in a Circuit Element

$$P_{VDD}(t) = I_{DD}(t)V_{DD}$$

$$P_{R}(t) = \frac{V_{R}^{2}(t)}{R} = I_{R}^{2}(t)R$$

$$V_{R} \neq V_{R}$$

$$E_C = \int_0^\infty I(t)V(t)dt = \int_0^\infty C\frac{dV}{dt}V(t)dt$$
$$= C\int_0^V V(t)dV = \frac{1}{2}CV_C^2$$

$$\bigvee_{C} \frac{1}{1} C \bigvee_{C} 1_{C} = C \text{ dV/d}$$

 $P_{\text{switching}} = \alpha C V_{DD}^2 f$ 

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#### Sources of Power Dissipation

- $\bullet P_{total} = P_{dynamic} + P_{static}$
- Dynamic power:  $P_{dynamic} = P_{switching} + P_{shortcircuit}$ 
  - Switching load capacitances
  - Short-circuit current
- Static power:  $P_{\text{static}} = (I_{\text{sub}} + I_{\text{gate}} + I_{\text{junct}} + I_{\text{contention}})V_{\text{DD}}$ 
  - Subthreshold leakage
  - Gate leakage
  - Junction leakage
  - Contention current

When the gate output rises



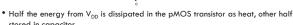
## Dynamic Power

• Energy stored in capacitor is  $E_C = \frac{1}{2} C_L V_{DD}^2$ 

Charging and Discharging a Capacitor

• But energy drawn from the supply is

$$\begin{split} E_{VDD} &= \int\limits_0^\infty I\left(t\right) \! V_{DD} dt = \int\limits_0^\infty C_L \frac{dV}{dt} V_{DD} dt \\ &= C_L V_{DD} \int\limits_0^\infty dV = C_L V_{DD}^2 \end{split}$$



When the gate output transitions HL

stored in capacitor

- Energy in capacitor is dumped to GND
- Dissipated as heat in the NMOS transistor



# **Dynamic Power Reduction**

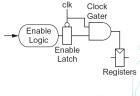
How can we limit switching power?

- Try to minimize:
  - Activity factor
  - Capacitance
  - Supply voltage
  - Frequency

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### Reduce Activity Factor

- Clock gating
- The best way to reduce the activity is to turn off the clock to registers in unused blocks
  - Saves clock activity (a = 1)
  - Eliminates all switching activity in the block
  - Requires determining if block will be used



 $P_{\text{switching}} = \alpha C V_{DD}^2 f$  of

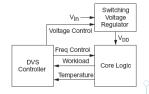
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### Reduce Capacitance

- $P_{\text{switching}} = \alpha C V_{DD}^2 f$
- Gate capacitance
  - Fewer stages of logic
  - Smaller gate sizes
- Wire capacitance
  - Good floorplanning to keep communicating blocks close to each other

$$P_{\text{switching}} = \alpha C V_{DD}^{2} f$$

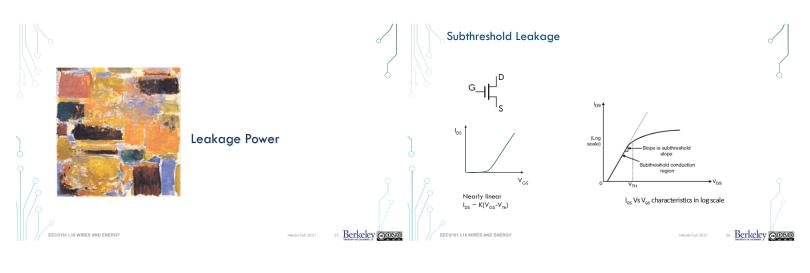
- performance requirements
- Voltage domains
  - Provide separate supplies to different blocks
- Dynamic voltage/frequency scaling
  - Adjust V<sub>DD</sub> and f according to workload

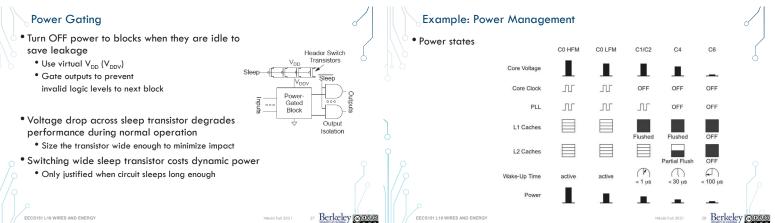


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- Wire contributes to delay, especially in modern technology
- We can use RC model to capture wire delays
- Energy becomes an increasingly important optimization goal
  - Dynamic energy
  - Static energy

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